

2SA770 2SA771

Silicon PNP Epitaxial Planar

☆ Complement to types 2SC1985 thru 2SC1986

Application Example:
 General and Industrial Purpose

● Outline Drawing 1MT-25(TO220)
 ● Test Circuit.....①

Absolute Maximum Ratings

Symbol	2SA770	2SA771	Unit
V _{CB0}	-60	-80	V
V _{CE0}	-60	-80	V
V _{EB0}	-6		V
I _C		-6	A
I _B		-3	A
P _C	40 (T _{FL} =25°C)		W
T _J	150		°C
T _{stg}	-55~+150		°C

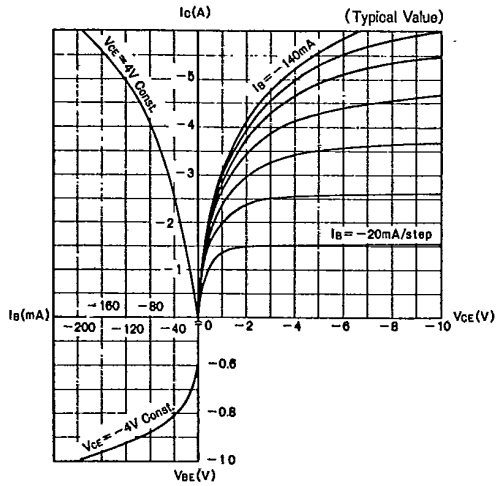
Electrical Characteristics

Symbol	Conditions	2SA770	2SA771	Unit
I _{CB0}	V _{CB} =	-1.0max	-1.0max	mA
I _{EB0}	V _{EB} =-6V		-1.0max	mA
V _{BE(CEO)}	I _C = -25mA	-60min	-80min	V
h _{FE}	V _{CE} =-4V, I _C =-1A		40min	
V _{CE(sat)}	I _C = -3A, I _B = -0.3A		-1.0max	V
f _T	V _{CE} =-12V, I _E =0.5A		10typ	MHz

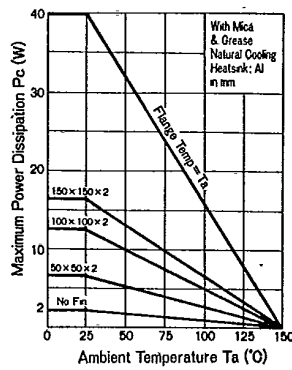
Typical Switching Characteristics (Emitter Common)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{B2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _r (μs)	t _{stg} (μs)	t _f (μs)
-9	3	-3	5	-400	400	0.9typ	1.0typ	0.1typ

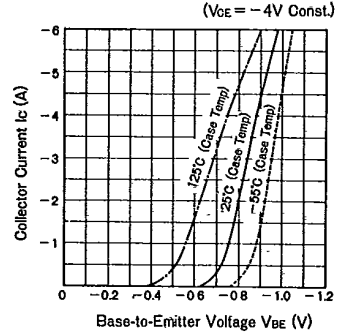
Common Emitter Characteristics



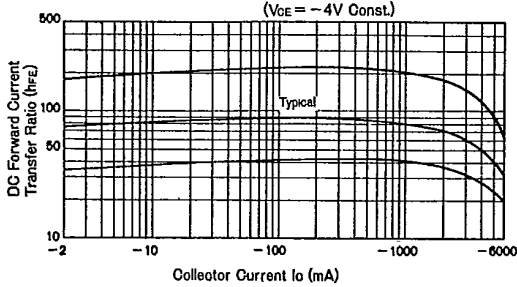
Power Derating



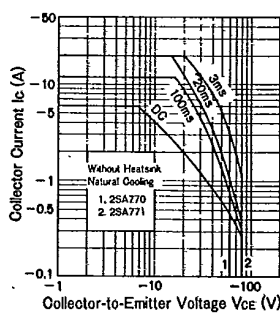
Temperature Characteristics



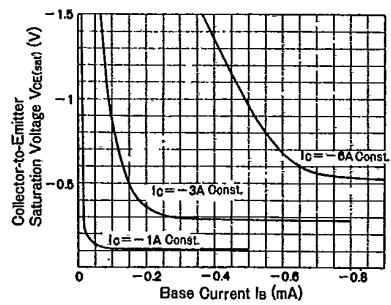
DC Current Gain Characteristics



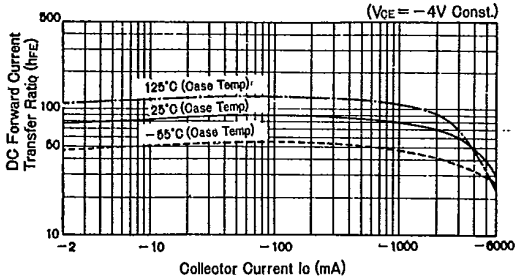
Maximum Areas For Safe Operation (ASO) (Single Pulse)



Collector-to-Emitter Saturation Characteristics (Typical Value)



DC Current Gain Temperature Characteristics



Transient Thermal Resistance Characteristics

